Jon Tomas Gudmundsson

List of Publications by Year in descending order

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163 papers 7,894 citations

66234 42 h-index 84 g-index

164 all docs

164 docs citations

164 times ranked 4194 citing authors

#	Article	IF	CITATIONS
1	Influence of the magnetic field on the discharge physics of a high power impulse magnetron sputtering discharge. Journal Physics D: Applied Physics, 2022, 55, 015202.	1.3	20
2	On the population density of the argon excited levels in a high power impulse magnetron sputtering discharge. Physics of Plasmas, 2022, 29, 023506.	0.7	1
3	lonization region model of high power impulse magnetron sputtering of copper. Surface and Coatings Technology, 2022, 442, 128189.	2.2	13
4	Particle-in-Cell Simulations With Fluid Metastable Atoms in Capacitive Argon Discharges: Electron Elastic Scattering and Plasma Density Profile Transition. IEEE Transactions on Plasma Science, 2022, 50, 2548-2557.	0.6	13
5	Modeling of high power impulse magnetron sputtering discharges with tungsten target. Plasma Sources Science and Technology, 2022, 31, 065009.	1.3	5
6	Operating modes and target erosion in high power impulse magnetron sputtering. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2022, 40, .	0.9	9
7	Foundations of physical vapor deposition with plasma assistance. Plasma Sources Science and Technology, 2022, 31, 083001.	1.3	27
8	HiPIMS optimization by using mixed high-power and low-power pulsing. Plasma Sources Science and Technology, 2021, 30, 015015.	1.3	19
9	On the electron energy distribution function in the high power impulse magnetron sputtering discharge. Plasma Sources Science and Technology, 2021, 30, 045011.	1.3	15
10	Generating ultradense pair beams using 400 <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mi>GeV</mml:mi><mml:mo>/</mml:mo><mml:mi .<="" 2021,="" 3,="" physical="" protons.="" research,="" review="" td=""><td>>c4/.6nml:r</td><td>ni>8/mml:mat</td></mml:mi></mml:math>	>c 4/.6 nml:r	ni>8/mml:mat
11	Bandgap atomistic calculations on hydrogen-passivated GeSi nanocrystals. Scientific Reports, 2021, 11, 13582.	1.6	10
12	Electron power absorption in radio frequency driven capacitively coupled chlorine discharge. Plasma Sources Science and Technology, 2021, 30, 065009.	1.3	14
13	Benchmarked and upgraded particle-in-cell simulations of a capacitive argon discharge at intermediate pressure: the role of metastable atoms. Plasma Sources Science and Technology, 2021, 30, 105009.	1.3	24
14	Tailoring interface alloying and magnetic properties in (111) Permalloy/Pt multilayers. Journal of Magnetism and Magnetic Materials, 2021, 538, 168288.	1.0	3
15	On the role of ion potential energy in low energy HiPIMS deposition: An atomistic simulation. Surface and Coatings Technology, 2021, 426, 127726.	2.2	7
16	On how to measure the probabilities of target atom ionization and target ion back-attraction in high-power impulse magnetron sputtering. Journal of Applied Physics, 2021, 129, .	1.1	17
17	On Electron Heating and Ion Recycling in High Power Impulse Magnetron Sputtering Discharge. , 2021, , .		O
18	Modeling of high power impulse magnetron sputtering discharges with graphite target. Plasma Sources Science and Technology, 2021, 30, 115017.	1.3	6

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19	Photoluminescence study of Si1-xGex nanoparticles in various oxide matrices. , 2021, , .		O
20	Surface effects in a capacitive argon discharge in the intermediate pressure regime. Plasma Sources Science and Technology, 2021, 30, 125011.	1.3	9
21	Physics of high power impulse magnetron sputtering discharges. , 2020, , 265-332.		8
22	Introduction to magnetron sputtering. , 2020, , 1-48.		14
23	Hardware and power management for high power impulse magnetron sputtering. , 2020, , 49-80.		10
24	Electron dynamics in high power impulse magnetron sputtering discharges. , 2020, , 81-110.		5
25	Heavy species dynamics in high power impulse magnetron sputtering discharges. , 2020, , 111-158.		4
26	Modeling the high power impulse magnetron sputtering discharge. , 2020, , 159-221.		4
27	Reactive high power impulse magnetron sputtering. , 2020, , 223-263.		5
28	Reticulated Mesoporous TiO ₂ Scaffold, Fabricated by Spray Coating, for Largeâ€Area Perovskite Solar Cells. Energy Technology, 2020, 8, 1900922.	1.8	19
29	Structural and photoluminescence study of TiO2 layer with self-assembled Si1â^' <i>x</i> Ge <i>x</i> nanoislands. Journal of Applied Physics, 2020, 128, .	1.1	5
30	Electron power absorption dynamics in a low pressure radio frequency driven capacitively coupled discharge in oxygen. Journal of Applied Physics, 2020, 128, .	1.1	11
31	Optimizing the deposition rate and ionized flux fraction by tuning the pulse length in high power impulse magnetron sputtering. Plasma Sources Science and Technology, 2020, 29, 05LT01.	1.3	46
32	Effect of substrate bias on microstructure of epitaxial film grown by HiPIMS: An atomistic simulation. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2020, 38, .	0.9	9
33	Collisionless electron cooling in a plasma thruster plume: experimental validation of a kinetic model. Plasma Sources Science and Technology, 2020, 29, 035029.	1.3	6
34	Study of the transition from self-organised to homogeneous plasma distribution in chromium HiPIMS discharge. Journal Physics D: Applied Physics, 2020, 53, 155201.	1.3	13
35	Obtaining SiGe nanocrystallites between crystalline TiO2 layers by HiPIMS without annealing. Applied Surface Science, 2020, 511, 145552.	3.1	8
36	Sideways deposition rate and ionized flux fraction in dc and high power impulse magnetron sputtering. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2020, 38, .	0.9	15

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37	A Ballistic Transport Model for an Artificial Neuron. Physica Status Solidi (A) Applications and Materials Science, 2020, 217, 1900936.	0.8	O
38	Optimization of HiPIMS discharges: The selection of pulse power, pulse length, gas pressure, and magnetic field strength. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2020, 38, .	0.9	35
39	Tailored voltage waveforms applied to a capacitively coupled chlorine discharge. Plasma Sources Science and Technology, 2020, 29, 084004.	1.3	18
40	Physics and technology of magnetron sputtering discharges. Plasma Sources Science and Technology, 2020, 29, 113001.	1.3	243
41	Oblique angle deposition of nickel thin films by high-power impulse magnetron sputtering. Beilstein Journal of Nanotechnology, 2019, 10, 1914-1921.	1.5	14
42	The hysteresis-free behavior of perovskite solar cells from the perspective of the measurement conditions. Journal of Materials Chemistry C, 2019, 7, 5267-5274.	2.7	13
43	The Effect of Magnetic Field Strength and Geometry on the Deposition Rate and Ionized Flux Fraction in the HiPIMS Discharge. Plasma, 2019, 2, 201-221.	0.7	45
44	Graphene bandgap induced by ferroelectric <i>Pca</i> 2 ₁ HfO ₂ substrates: a first-principles study. Physical Chemistry Chemical Physics, 2019, 21, 15001-15006.	1.3	12
45	Efficacy of annealing and fabrication parameters on photo-response of SiGe in TiO ₂ matrix. Nanotechnology, 2019, 30, 365604.	1.3	8
46	Role of ionization fraction on the surface roughness, density, and interface mixing of the films deposited by thermal evaporation, dc magnetron sputtering, and HiPIMS: An atomistic simulation. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2019, 37, .	0.9	23
47	Effect of atomic ordering on the magnetic anisotropy of single crystal Ni80Fe20. AIP Advances, 2019, 9,	0.6	12
48	Electron heating mode transitions in a low pressure capacitively coupled oxygen discharge. Plasma Sources Science and Technology, 2019, 28, 045012.	1.3	30
49	Enhanced photoconductivity of embedded SiGe nanoparticles by hydrogenation. Applied Surface Science, 2019, 479, 403-409.	3.1	11
50	Fabrication and characterization of Si _{1â^'} <i>_x</i> Ce <i>_x</i> nanocrystals in as-grown and annealed structures: a comparative study. Beilstein Journal of Nanotechnology, 2019, 10, 1873-1882.	1.5	5
51	Enhanced photoconductivity of SiGe nanocrystals in SiO2 driven by mild annealing. Applied Surface Science, 2019, 469, 870-878.	3.1	12
52	A global model study of low pressure high density CF4 discharge. Plasma Sources Science and Technology, 2019, 28, 025007.	1.3	13
53	The frequency dependence of the discharge properties in a capacitively coupled oxygen discharge. Plasma Sources Science and Technology, 2018, 27, 025009.	1.3	30
54	Non-Maxwellian electron energy probability functions in the plume of a SPT-100 Hall thruster. Plasma Sources Science and Technology, 2018, 27, 015006.	1.3	12

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55	Growth of HfN thin films by reactive high power impulse magnetron sputtering. AIP Advances, $2018, 8, .$	0.6	12
56	The Influence of Secondary Electron Emission and Electron Reflection on a Capacitively Coupled Oxygen Discharge. Atoms, 2018, 6, 65.	0.7	14
57	On three different ways to quantify the degree of ionization in sputtering magnetrons. Plasma Sources Science and Technology, 2018, 27, 105005.	1.3	44
58	Comparison of magnetic and structural properties of permalloy Ni ₈₀ Fe ₂₀ grown by dc and high power impulse magnetron sputtering. Journal Physics D: Applied Physics, 2018, 51, 285005.	1.3	16
59	The role of surface quenching of the singlet delta molecule in a capacitively coupled oxygen discharge. Plasma Sources Science and Technology, 2018, 27, 074002.	1.3	18
60	On Recycling in High Power Impulse Magnetron Sputtering Discharges. , 2018, , .		3
61	On the role of metastable states in low pressure oxygen discharges. AIP Conference Proceedings, 2017,	0.3	10
62	Normal and Inverted Hysteresis in Perovskite Solar Cells. Journal of Physical Chemistry C, 2017, 121, 11207-11214.	1.5	68
63	On singlet metastable states, ion flux and ion energy in single and dual frequency capacitively coupled oxygen discharges. Journal Physics D: Applied Physics, 2017, 50, 175201.	1.3	14
64	Preface to Special Topic: Reactive high power impulse magnetron sputtering. Journal of Applied Physics, 2017, 121, 171801.	1.1	5
65	A study of the oxygen dynamics in a reactive Ar/O2 high power impulse magnetron sputtering discharge using an ionization region model. Journal of Applied Physics, 2017, 121, .	1.1	32
66	A unified treatment of self-sputtering, process gas recycling, and runaway for high power impulse sputtering magnetrons. Plasma Sources Science and Technology, 2017, 26, 125003.	1.3	79
67	Foundations of DC plasma sources. Plasma Sources Science and Technology, 2017, 26, 123001.	1.3	64
68	Reversal of Thermoelectric Current in Tubular Nanowires. Physical Review Letters, 2017, 119, 036804.	2.9	25
69	On electron heating in a low pressure capacitively coupled oxygen discharge. Journal of Applied Physics, 2017, 122, .	1.1	34
70	Vanadium and vanadium nitride thin films grown by high power impulse magnetron sputtering. Journal Physics D: Applied Physics, 2017, 50, 505302.	1.3	19
71	Particle-balance models for pulsed sputtering magnetrons. Journal Physics D: Applied Physics, 2017, 50, 354003.	1.3	59
72	Influence of preparation conditions on structure and photosensing properties of GeSi/TiO <inf>2</inf> multilayers. , 2017, , .		3

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7 3	On Electron Heating In Magnetron Sputtering Discharges. , 2017, , .		O
74	lodine Migration and Degradation of Perovskite Solar Cells Enhanced by Metallic Electrodes. Journal of Physical Chemistry Letters, 2016, 7, 5168-5175.	2.1	225
7 5	An ionization region model of the reactive Ar/O ₂ high power impulse magnetron sputtering discharge. Plasma Sources Science and Technology, 2016, 25, 065004.	1.3	94
76	The role of the metastable O (sub 2 (sub 6 (b 6) (b 6) (b 6) and energy-dependent secondary electron emission yields in capacitively coupled oxygen discharges. Plasma Sources Science and Technology, 2016, 25, 055002.	1.3	39
77	Conductance oscillations of core-shell nanowires in transversal magnetic fields. Physical Review B, 2016, 93, .	1.1	12
78	The role of Ohmic heating in dc magnetron sputtering. Plasma Sources Science and Technology, 2016, 25, 065024.	1.3	41
79	On reactive high power impulse magnetron sputtering. Plasma Physics and Controlled Fusion, 2016, 58, 014002.	0.9	31
80	Morphology of Tantalum Nitride Thin Films Grown on Fused Quartz by Reactive High Power Impulse Magnetron Sputtering (HiPIMS). Materials Research Society Symposia Proceedings, 2015, 1803, 1.	0.1	0
81	Are the argon metastables important in high power impulse magnetron sputtering discharges?. Physics of Plasmas, 2015, 22, .	0.7	26
82	The pressure dependence of the discharge properties in a capacitively coupled oxygen discharge. Journal of Applied Physics, 2015, 118, 153302.	1.1	28
83	A volume averaged global model study of the influence of the electron energy distribution and the wall material on an oxygen discharge. Journal Physics D: Applied Physics, 2015, 48, 495203.	1.3	9
84	On the role of metastables in capacitively coupled oxygen discharges. Plasma Sources Science and Technology, 2015, 24, 035016.	1.3	24
85	On the formation and annihilation of the singlet molecular metastables in an oxygen discharge. Journal Physics D: Applied Physics, 2015, 48, 325202.	1.3	28
86	Dual-frequency capacitively coupled chlorine discharge. Plasma Sources Science and Technology, 2015, 24, 015003.	1.3	11
87	A current driven capacitively coupled chlorine discharge. Plasma Sources Science and Technology, 2014, 23, 025015.	1.3	21
88	lon Energy and Angular Distributions in a Dual-Frequency Capacitively Coupled Chlorine Discharge. IEEE Transactions on Plasma Science, 2014, 42, 2854-2855.	0.6	7
89	On the road to self-sputtering in high power impulse magnetron sputtering: particle balance and discharge characteristics. Plasma Sources Science and Technology, 2014, 23, 025017.	1.3	55
90	On sheath energization and Ohmic heating in sputtering magnetrons. Plasma Sources Science and Technology, 2013, 22, 045005.	1.3	72

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91	Rutile TiO 2 thin films grown by reactive high power impulse magnetron sputtering. Thin Solid Films, 2013, 545, 445-450.	0.8	51
92	The properties of TiN ultra-thin films grown on SiO2 substrate by reactive high power impulse magnetron sputtering under various growth angles. Thin Solid Films, 2013, 548, 354-357.	0.8	14
93	A benchmark study of a capacitively coupled oxygen discharge of the oopd1 particle-in-cell Monte Carlo code. Plasma Sources Science and Technology, 2013, 22, 035011.	1.3	77
94	Ultra-thin poly-crystalline TiN films grown by HiPIMS on MgO(100) — In-situ resistance study of the initial stage of growth. Thin Solid Films, 2013, 549, 199-203.	0.8	10
95	A particle-in-cell/Monte Carlo simulation of a capacitively coupled chlorine discharge. Plasma Sources Science and Technology, 2013, 22, 055020.	1.3	27
96	Current–voltage–time characteristics of the reactive Ar/O2 high power impulse magnetron sputtering discharge. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2012, 30, 050601.	0.9	37
97	Comparing resonant photon tunneling via cavity modes and Tamm plasmon polariton modes in metal-coated Bragg mirrors. Optics Letters, 2012, 37, 4026.	1.7	27
98	Nucleation and Resistivity of Ultrathin TiN Films Grown by High-Power Impulse Magnetron Sputtering. IEEE Electron Device Letters, 2012, 33, 1045-1047.	2.2	31
99	High power impulse magnetron sputtering discharge. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2012, 30, .	0.9	568
100	Gas rarefaction and the time evolution of long high-power impulse magnetron sputtering pulses. Plasma Sources Science and Technology, 2012, 21, 045004.	1.3	82
101	The influence of the electron energy distribution on the low pressure chlorine discharge. Vacuum, 2012, 86, 808-812.	1.6	14
102	An ionization region model for high-power impulse magnetron sputtering discharges. Plasma Sources Science and Technology, 2011, 20, 065007.	1.3	101
103	Current-voltage-time characteristics of the reactive Ar/N2 high power impulse magnetron sputtering discharge. Journal of Applied Physics, 2011, 110, 083306.	1.1	53
104	Morphology of TiN thin films grown on SiO2 by reactive high power impulse magnetron sputtering. Thin Solid Films, 2011, 520, 1621-1624.	0.8	62
105	Growth and in-situ electrical characterization of ultrathin epitaxial TiN films on MgO. Thin Solid Films, 2011, 519, 5861-5867. [www.w3.org/1998/Math/MathML]	0.8	25
106	display="inline"> <mml:msup><mml:mi>Ar</mml:mi><mml:mo>+</mml:mo></mml:msup> and <mml: xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:msup><mml:mi>Xe</mml:mi><mml:mo>+</mml:mo></mml:msup>Velocities near the Presheath-Sheath Boundary in an<mml:math< td=""><td></td><td>30</td></mml:math<></mml: 		30
107	xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline">	0.1	1
108	Comparison of TiN thin films grown on SiO2 by reactive dc magnetron sputtering and high power impulse magnetron sputtering. Materials Research Society Symposia Proceedings, 2011, 1335, 81.	0.1	0

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109	On the film density using high power impulse magnetron sputtering. Surface and Coatings Technology, 2010, 205, 591-596.	2.2	317
110	The high power impulse magnetron sputtering discharge as an ionized physical vapor deposition tool. Vacuum, 2010, 84, 1360-1364.	1.6	93
111	The low pressure Cl ₂ /O ₂ discharge and the role of ClO. Plasma Sources Science and Technology, 2010, 19, 055008.	1.3	32
112	Low pressure hydrogen discharges diluted with argon explored using a global model. Plasma Sources Science and Technology, 2010, 19, 065008.	1.3	99
113	Morphology of TiN thin films grown on MgO(001) by reactive dc magnetron sputtering. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2010, 28, 912-915.	0.9	17
114	A global (volume averaged) model of a Cl ₂ /Ar discharge: I. Continuous power. Journal Physics D: Applied Physics, 2010, 43, 115201.	1.3	34
115	Effect of hydrogenation on minority carrier lifetime in low-grade silicon. Physica Scripta, 2010, T141, 014005.	1.2	5
116	A global (volume averaged) model of a chlorine discharge. Plasma Sources Science and Technology, 2010, 19, 015001.	1.3	78
117	A global (volume averaged) model of a Cl ₂ /Ar discharge: II. Pulsed power modulation. Journal Physics D: Applied Physics, 2010, 43, 115202.	1.3	11
118	A global (volume averaged) model of a nitrogen discharge: I. Steady state. Plasma Sources Science and Technology, 2009, 18, 045001.	1.3	86
119	Electrical and structural properties of ultrathin polycrystalline and epitaxial TiN films grown by reactive dc magnetron sputtering. Materials Research Society Symposia Proceedings, 2009, 1156, 1.	0.1	0
120	In-situ electrical characterization of ultrathin TiN films grown by reactive dc magnetron sputtering on SiO2. Thin Solid Films, 2009, 517, 6731-6736.	0.8	41
121	On the electron energy in the high power impulse magnetron sputtering discharge. Journal of Applied Physics, 2009, 105, .	1.1	76
122	A global (volume averaged) model of a nitrogen discharge: II. Pulsed power modulation. Plasma Sources Science and Technology, 2009, 18, 045002.	1.3	18
123	Growth, coalescence, and electrical resistivity of thin Pt films grown by dc magnetron sputtering on SiO2. Applied Surface Science, 2008, 254, 7356-7360.	3.1	31
124	lonized physical vapor deposition (IPVD): magnetron sputtering discharges. Journal of Physics: Conference Series, 2008, 100, 082002.	0.3	23
125	Ionization mechanism in the high power impulse magnetron sputtering (HiPIMS) discharge. Journal of Physics: Conference Series, 2008, 100, 082013.	0.3	49
126	Electrical resistivity and morphology of ultra thin Pt films grown by dc magnetron sputtering on SiO ₂ . Journal of Physics: Conference Series, 2008, 100, 082006.	0.3	31

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127	Plasma parameters in a planar dc magnetron sputtering discharge of argon and krypton. Journal of Physics: Conference Series, 2008, 100, 062018.	0.3	27
128	Digital smoothing of the Langmuir probe I-V characteristic. Review of Scientific Instruments, 2008, 79, 073503.	0.6	44
129	A magnetron sputtering system for the preparation of patterned thin films and <i>in situ</i> thin film electrical resistance measurements. Review of Scientific Instruments, 2007, 78, 103901.	0.6	36
130	Oxygen discharges diluted with argon: dissociation processes. Plasma Sources Science and Technology, 2007, 16, 399-412.	1.3	247
131	In situ resistivity measurements during growth of ultra-thin Cr0.7Mo0.3. Thin Solid Films, 2006, 515, 583-586.	0.8	5
132	Ionized physical vapor deposition (IPVD): A review of technology and applications. Thin Solid Films, 2006, 513, 1-24.	0.8	886
133	The ion energy distributions and ion flux composition from a high power impulse magnetron sputtering discharge. Thin Solid Films, 2006, 515, 1522-1526.	0.8	279
134	Plasma ignition in a grounded chamber connected to a capacitive discharge. Plasma Sources Science and Technology, 2006, 15, 276-287.	1.3	8
135	Improved volume-averaged model for steady and pulsed-power electronegative discharges. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2006, 24, 2025-2040.	0.9	107
136	Spatial electron density distribution in a high-power pulsed magnetron discharge. IEEE Transactions on Plasma Science, 2005, 33, 346-347.	0.6	100
137	Plasma dynamics in a highly ionized pulsed magnetron discharge. Plasma Sources Science and Technology, 2005, 14, 525-531.	1.3	98
138	Ion-assisted physical vapor deposition for enhanced film properties on nonflat surfaces. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2005, 23, 278-280.	0.9	211
139	Ion-acoustic solitary waves in a high power pulsed magnetron sputtering discharge. Journal Physics D: Applied Physics, 2005, 38, 3417-3421.	1.3	36
140	Lithium-diffused and annealed GaAs: An admittance spectroscopy study. Physical Review B, 2004, 69, .	1.1	4
141	Recombination and detachment in oxygen discharges: the role of metastable oxygen molecules. Journal Physics D: Applied Physics, 2004, 37, 2073-2081.	1.3	93
142	Preparation and characterization of magnetron sputtered, ultra-thin Cr0.63Mo0.37 films on MgO. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2004, 22, 1636-1639.	0.9	5
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144	Impurity band in lithium-diffused and annealed GaAs: Conductivity and Hall effect measurements. Physical Review B, 2003, 67, .	1.1	9

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145	Global model of plasma chemistry in a low-pressure O2/F2discharge. Journal Physics D: Applied Physics, 2002, 35, 328-341.	1.3	49
146	Spatial and temporal behavior of the plasma parameters in a pulsed magnetron discharge. Surface and Coatings Technology, 2002, 161, 249-256.	2.2	189
147	Potential Fluctuations and Site Switching in Si-doped GaAs Studied by Photoluminescence. Physica Scripta, 2002, T101, 114.	1.2	2
148	Electronegativity of low-pressure high-density oxygen discharges. Journal Physics D: Applied Physics, 2001, 34, 1100-1109.	1.3	185
149	On the effect of the electron energy distribution on the plasma parameters of an argon discharge: a global (volume-averaged) model study. Plasma Sources Science and Technology, 2001, 10, 76-81.	1.3	165
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151	The effect of Si site-switching in GaAs on electrical properties and potential fluctuation. Physica B: Condensed Matter, 2001, 308-310, 804-807.	1.3	1
152	A reply to a comment on: `On the plasma parameters of a planar inductive oxygen discharge. Journal Physics D: Applied Physics, 2000, 33, 3010-3012.	1.3	14
153	On the plasma parameters of a planar inductive oxygen discharge. Journal Physics D: Applied Physics, 2000, 33, 1323-1331.	1.3	91
154	The ion energy distribution in a planar inductive oxygen discharge. Journal Physics D: Applied Physics, 1999, 32, 798-803.	1.3	11
155	Lithium–gold-related complexes in p-type crystalline silicon. Physica B: Condensed Matter, 1999, 273-274, 379-382.	1.3	О
156	Hydrogen passivation of AlxGa1â^'xAs/GaAs studied by surface photovoltage spectroscopy. Physica B: Condensed Matter, 1999, 273-274, 689-692.	1.3	11
157	lon energy distribution in H2/Ar plasma in a planar inductive discharge. Plasma Sources Science and Technology, 1999, 8, 58-64.	1.3	36
158	Experimental studies of O2/Ar plasma in a planar inductive discharge. Plasma Sources Science and Technology, 1999, 8, 22-30.	1.3	102
159	Hydrogenation of polysilicon thin-film transistor in a planar inductive H/sub 2//Ar discharge. IEEE Electron Device Letters, 1999, 20, 223-225.	2.2	27
160	Magnetic induction and plasma impedance in a planar inductive discharge. Plasma Sources Science and Technology, 1998, 7, 83-95.	1.3	30
161	Model and measurements for a planar inductive oxygen discharge. Plasma Sources Science and Technology, 1998, 7, 1-12.	1.3	68
162	Experimental studies of Ar plasma in a planar inductive discharge. Plasma Sources Science and Technology, 1998, 7, 330-336.	1.3	23

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163	Magnetic induction and plasma impedance in a cylindrical inductive discharge. Plasma Sources Science and Technology, 1997, 6, 540-550.	1.3	53